

ABSTRACT

Disclosed is a substrate processing apparatus which comprises reaction tubes (3,4) for processing multiple substrates (27), a heater (5) for heating the substrates, and gas introducing nozzles (6,7,8,9,10) for supplying a gas into the reaction tubes. Each of the gas introducing nozzles (6,7,8,9) is structured so that at least the channel cross section of a portion facing the heater (5) is larger than those of the other portions.